

## ABSTRACT

In a CMP process for polishing copper and a barrier metal formed on a substrate to form a buried copper interconnect, a polishing pad is subjected to dressing under a dressing  
5 pressure of  $29\text{g/cm}^2$  so that the surface roughness of the polishing pad becomes  $3\mu\text{m}$  to  $5\mu\text{m}$  inclusive. Thereby, dishing of the copper interconnect can be reduced as compared with a known method without reducing the removal rate of the copper and barrier metal.